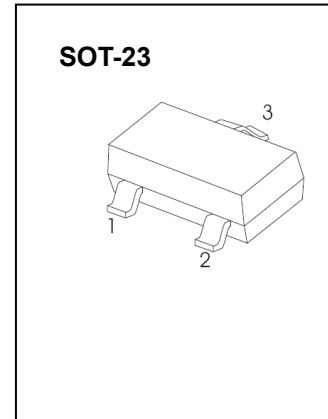
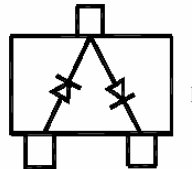


FEATURES

- Low forward voltage : $V_F (3) = 0.9V$ (typ.)
- Fast reverse recovery time : $t_{rr} = 1.6ns$ (typ.)
- Small total capacitance : $C_T = 0.9pF$ (typ.)



MARKING: C3

Maximum Ratings ,Single Diode @ $T_A=25^{\circ}C$

Parameter	Symbol	Limits	Unit
Non-Repetitive Peak reverse voltage	V_{RM}	85	V
Peak Repetitive Peak reverse voltage	V_{RRM}	80	V
Working Peak Reverse Voltage	V_{RWM}		
DC Blocking Voltage	V_R		
Forward Continuous Current	I_{FM}	300	mA
Average Rectified Output Current	I_O	100	mA
Peak forward surge current @=10ms	I_{FSM}	2	A
Power Dissipation	P_D	150	mW
Junction temperature	T_J	150	$^{\circ}C$
Storage temperature	T_{STG}	-55-150	$^{\circ}C$

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)}$	$I_R = 100\mu A$	80		V
Reverse voltage leakage current	I_R	$V_R = 80V$		0.5	μA
Forward voltage	V_F	$I_F = 100mA$		1.2	V
Diode capacitance	C_D	$V_R = 0V, f = 1MHz$		3	pF
Reverse recovery time	t_{rr}	$I_F = 10mA$		4	nS

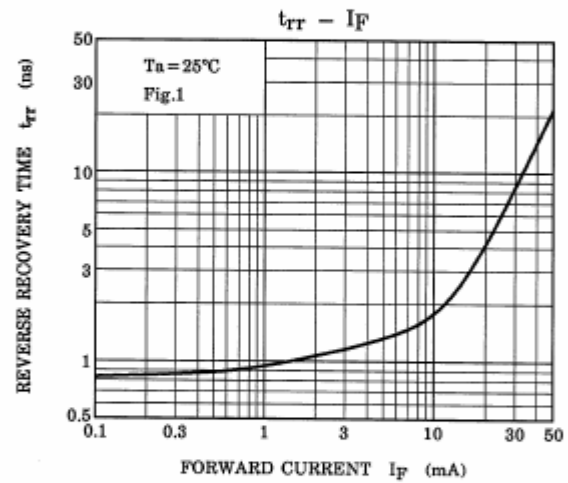
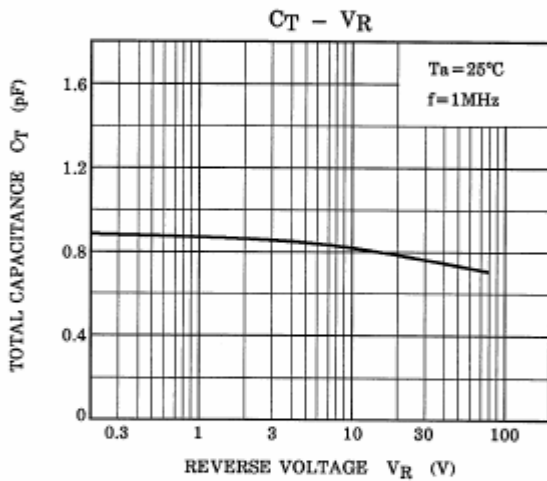
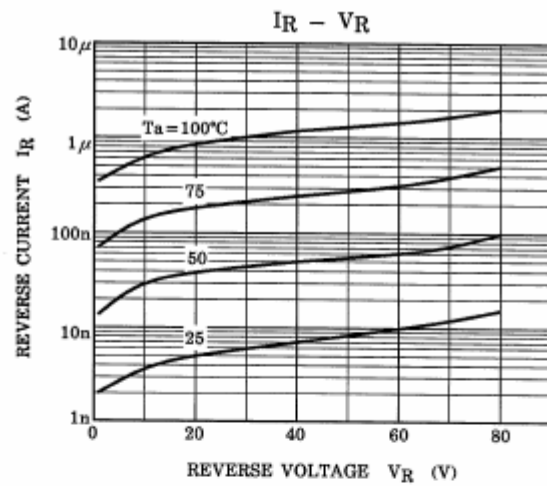
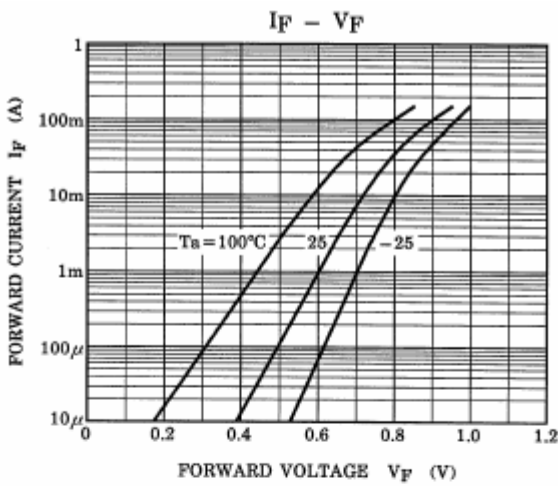


Fig.1 Reverse recovery time (t_{RR}) test circuit

